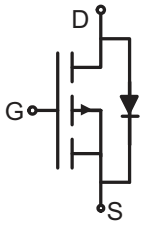
RECTRON SEMICONDUCTOR
TECHNICAL SPECIFICATION

RM2A3P60S4

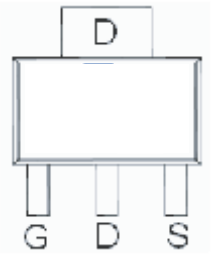
P-Channel Enhancement Mode Power MOSFET

Description

The RM2A3P60S4 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.



Schematic diagram



SOT-223 top view

General Features

- V_{DS} = -60V,I_D = -2.3A
  $R_{DS(ON)}$ < 180mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ < 260mΩ @ V_{GS}=-5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply
- Halogen-free
- P/N suffix V means AEC-Q101 qualified, e.g:RM2A3P60S4V

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2A3P60	RM2A3P60S4	SOT-223-3L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-2.3	A
Drain Current-Pulsed (Note 1)	I_{DM}	-12	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	85	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-48V,V_{GS}=0V	-	-	1	μA

Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.5	-2.0	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-2A	-	140	180	mΩ
		V_{GS}=-4.5V, I_D=-1.5A	-	200	260	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D =-2A	-	5.3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-15V,V_{GS}=0V, F=1.0MHz	-	428	600	PF
Output Capacitance	C_{oss}		-	39	55	PF
Reverse Transfer Capacitance	C_{rss}		-	26	36.4	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-30V,I_D=-2A, V_{GS}=-10V,R_G=3.3Ω	-	4.1	8.2	nS
Turn-on Rise Time	t_r		-	21	38	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20.3	40.6	nS
Turn-Off Fall Time	t_f		-	21	42	nS
Total Gate Charge	Q_g	V_{DS}=-48V,I_D=-2A, V_{GS}=-10V	-	8.3	11.6	nC
Gate-Source Charge	Q_{gs}		-	1.8	2.52	nC
Gate-Drain Charge	Q_{gd}		-	1.6	2.25	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-1A	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-2.3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to product

RATING AND CHARACTERISTICS CURVES (RM2A3P60S4)

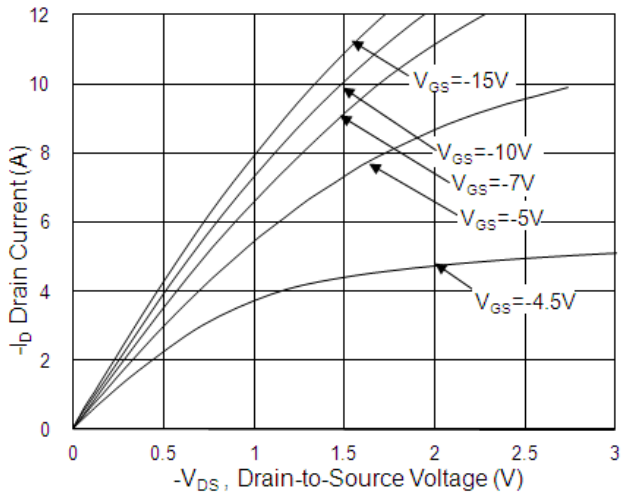


Fig.1 Typical Output Characteristics

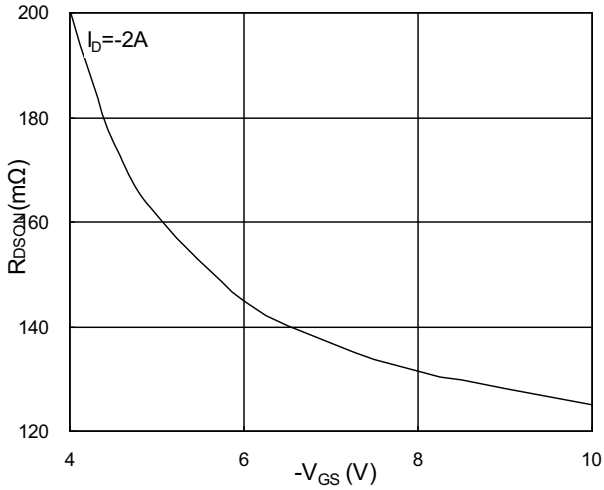


Fig.2 On-Resistance vs. Gate-Source Voltage

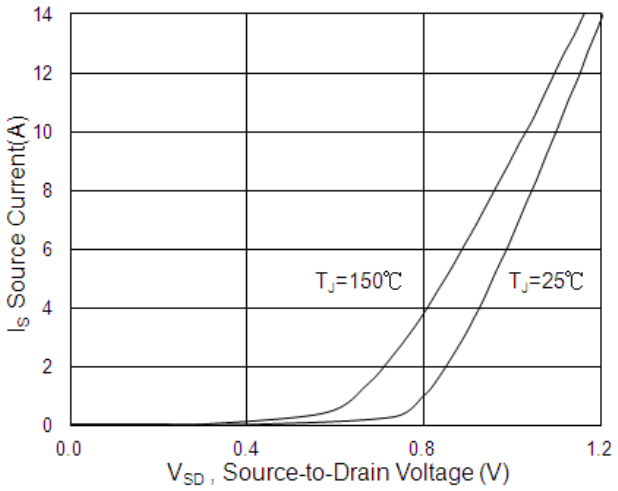


Fig.3 Forward Characteristics Of Reverse

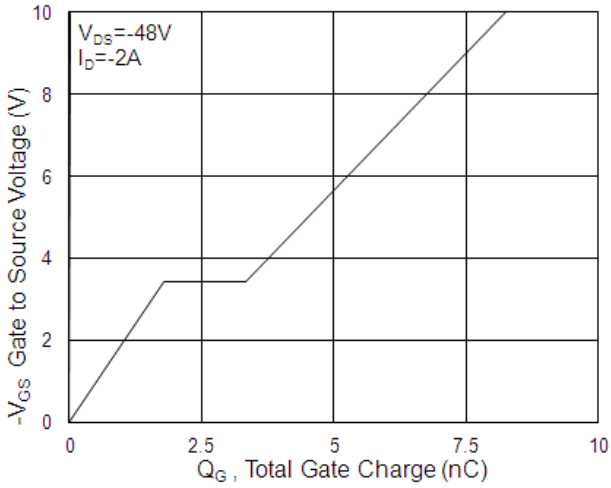


Fig.4 Gate-Charge Characteristics

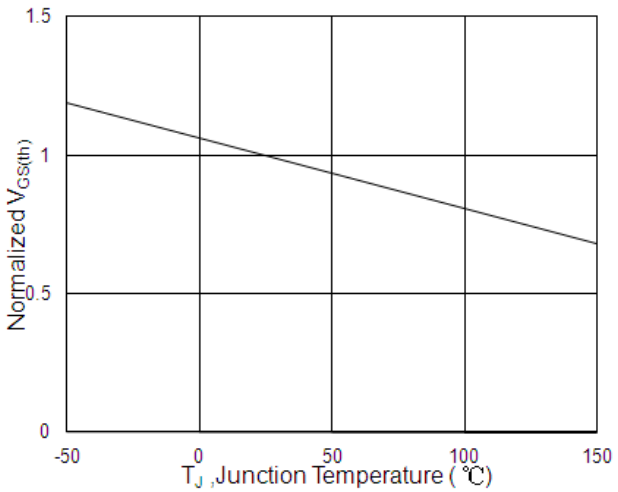


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

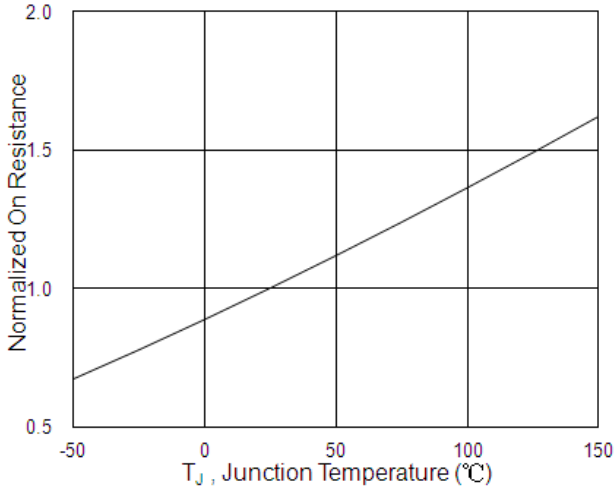


Fig.6 Normalized R_{DSON} vs. T_J

RATING AND CHARACTERISTICS CURVES (RM2A3P60S4)

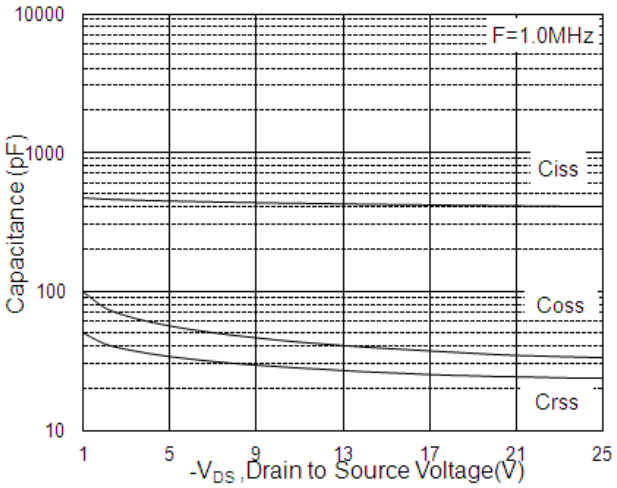


Fig.7 Capacitance

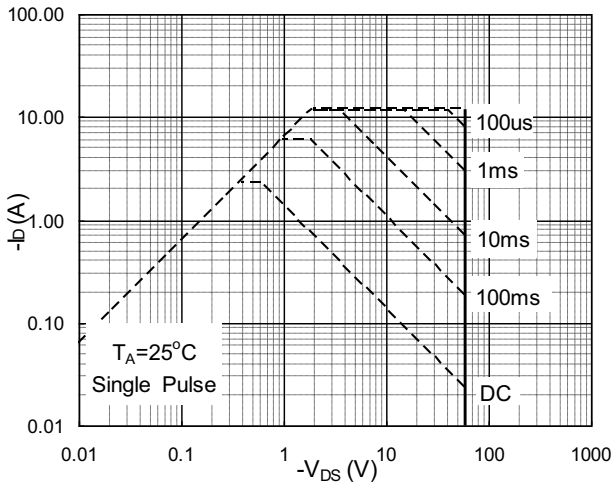


Fig.8 Safe Operating Area

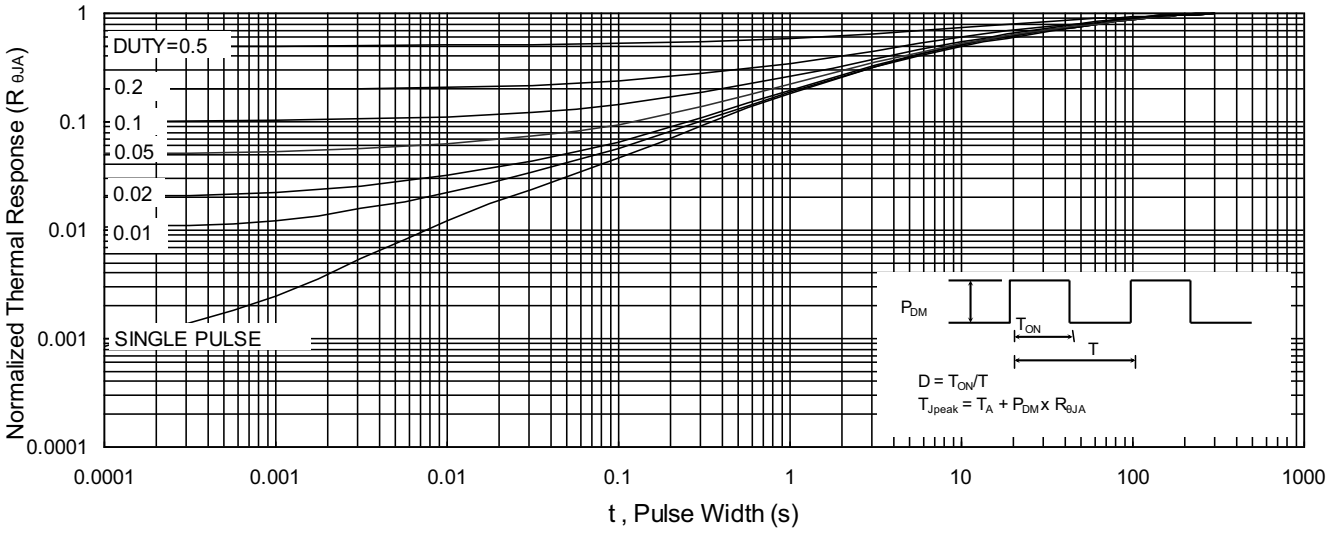


Fig.9 Normalized Maximum Transient Thermal Impedance

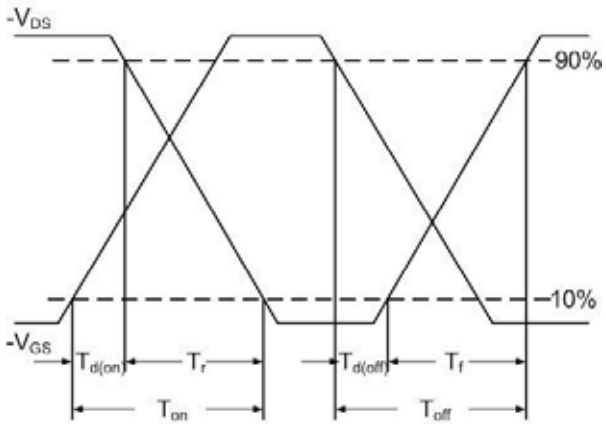


Fig.10 Switching time waveform

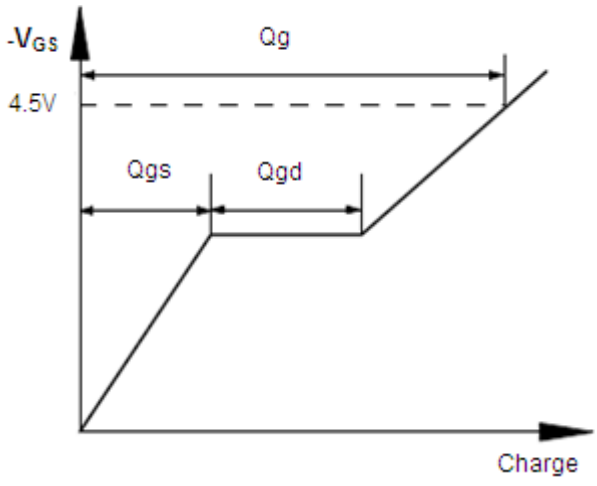
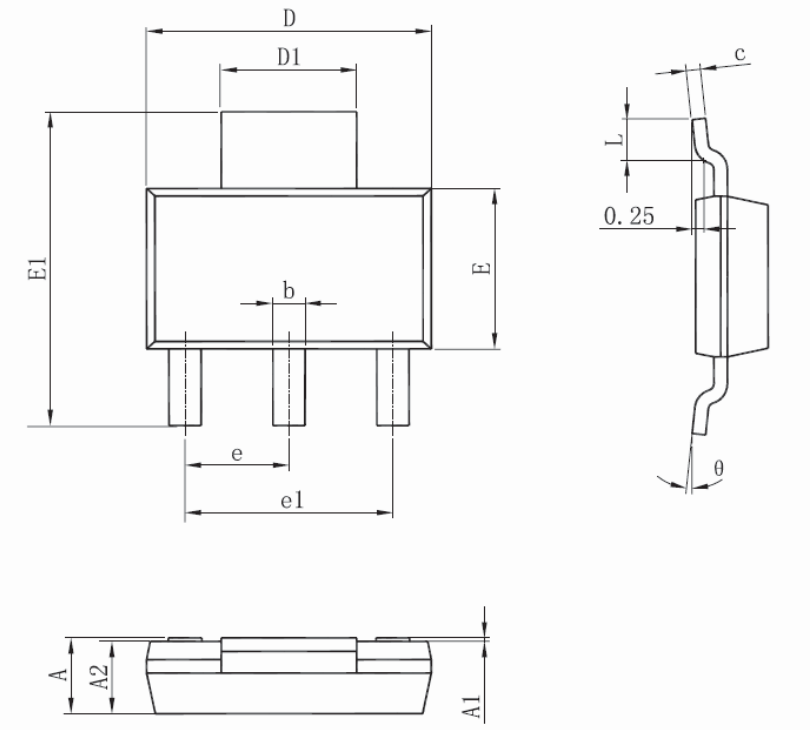


Fig.11 Gate Charge waveform

SOT-223 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300(BSC)		0.091(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°

Notes

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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